INFRARED DIODE LASER AT 808nm

RN-III-808R/1~500mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy

operation. They are used in measurement, communication, spectrum analysis, etc.

产品参数

RN-III-808R/1~500mW			
Wavelength (nm)		808±3	
Operating mode		CW	
Output power (mW)		>1, 10, 20,, 200	>200, 210 ,, 500
Power stability (rms, over 4 hours)		<1%, <3%, <5%	
Transverse mode		Round	
Dimensions of beam at the aperture (mm)		~2	~2
Beam divergence, full angle (mrad)		~10	~20
Warm-up time (minutes)		<5	
Beam height from base plate (mm)		24.8	
Operating temperature ($^{\circ}\!\!\mathbb{C}$)		10~35	
Power supply	85-264VAC	PSU-III-LED/ PSU-III-FDA (Frequency for 1Hz-30kHz)	
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)	
TTL / Analog modulation		TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional	
Expected lifetime (hours)		10000	
Warranty		1 year	

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